



## E. Compound Semiconductors 분과

2019년 2월 15일(금), 15:30-17:15

Room H (루비1+2, 5층)

## [FH3-E] Compound Characterization Technology

좌장: 차호영 교수(홍익대학교)

<p><b>FH3-E-1</b> 15:30-15:45</p>	<p><b>Excellent Sub-Threshold Characteristics of MIS-Fin HFET by Using M-Plane Sidewall Channel</b></p> <p>Quan Dai, Dong-Hyeok Son, Ryun-Hwi Kim, Jun-Hyeok Lee, Jeong-Gil Kim, Terirama Thingujam, Seung-Hyeon Kang, Hyeon-Su Lee, and Jung-Hee Lee <i>School of electronics engineering, Kyungpook National University</i></p>
<p><b>FH3-E-2</b> 15:45-16:00</p>	<p><b>High-sensitivity Hydrogen Gas Sensor based on AlGaIn/GaN Recessed HEMT with a Source-Connected Pt-Gate</b></p> <p>Anh Tuan Vuong, Dongmin Keum, Cuong Van Nguyen, and Hyungtak Kim <i>School of Electronic and Electrical Engineering, Hongik University</i></p>
<p><b>FH3-E-3</b> 16:00-16:15</p>	<p><b>Analysis of GaN Vertical Nanowire through 3-D Simulation</b></p> <p>Terirama Thingujam, Dong-Hyeok Son, Young Jun Yoon, Dai Quan, Junhyeok Lee, Kyung-Wan Kim, Jeong-Gil Kim, In Man Kang, and Jung-Hee Lee <i>School of Electronics Engineering, Kyungpook National University</i></p>
<p><b>FH3-E-4</b> 16:15-16:30</p>	<p><b>습식 세정액 내 InGaAs 반도체 표면의 산화 및 식각 거동 연구</b></p> <p>Jihoon Na, Jinhoon Lee, Junwoo Lee, and Sangwoo Lim <i>Department of Chemical and Biomolecular Engineering, Yonsei University</i></p>
<p><b>FH3-E-5</b> 16:30-16:45</p>	<p><b>Performance of AlGaIn/GaN MISHEMT with Wide Channel Using Fin Structure</b></p> <p>Hyeon-Su Lee, Ryun-Hwi Kim, Chul-Ho Won, Jung-Gil Kim, Kyung-Wan Kim, and Jung-Hee Lee <i>School of Electrical Engineering, Kyungpook National University</i></p>
<p><b>FH3-E-6</b> 16:45-17:00</p>	<p><b>Characterization of Subgap Density-of-States from Sub-Bandgap Optical Charge Pumping in <math>\text{In}_{0.53}\text{Ga}_{0.47}\text{As}</math> MOSFETs</b></p> <p>Han Bin Yoo<sup>1</sup>, Seong Kwang Kim<sup>2</sup>, Junyeap Kim<sup>1</sup>, Jintae Yu<sup>1</sup>, Jieun Kim<sup>1</sup>, Sung-Jin Choi<sup>1</sup>, Dae Hwan Kim<sup>1</sup>, and Dong Myong Kim<sup>1</sup> <sup>1</sup><i>School of Electrical Engineering, Kookmin University,</i> <sup>2</sup><i>Center for Opto-Electronic Materials and Devices, KIST</i></p>
<p><b>FH3-E-7</b> 17:00-17:15</p>	<p><b>표면 Passivation을 통한 InGaAs의 특성 향상 연구</b></p> <p>이진훈, 나지훈, 임상우 <i>연세대학교 화학생명공학과</i></p>